

**Process For Manufacturing A Piezoelectric Structure For A Radiofrequency Device
And Which Can Be Used To Transfer A Piezoelectric Layer, And Process For
Transferring Such A Piezoelectric Layer**

Abstract

A process for manufacturing a piezoelectric structure (10, 10'), said process being characterized in that it comprises providing a substrate of piezoelectric material (20), providing a carrier substrate (100), depositing a dielectric bonding layer (1001) at a temperature lower than or equal to 300°C on a single side of the substrate of piezoelectric material (20), a step (1') of joining the substrate of piezoelectric material (20) to the carrier substrate (100) via the dielectric bonding layer (1001), a thinning step (2') for forming the piezoelectric structure (10, 10'), which comprises a layer of piezoelectric material (200) joined to a carrier substrate (100).

[Fig. 1]